

Search Notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	("mramandresistiveadjmaterialsam ememoryanddiode").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/02 21:38
L2	15	mram and resistive adj material same memory and diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:38
L3	74	mram and resistor same memory same diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:38
L4	10	mram and resistor with series with diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:45
L5	2	mram and resistor with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:47
L6	4699	memory and resistor with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:48
L7	492	memory and resistance adj value with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:48
L8	105	memory same resistance adj value with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:48
L9	54	memory with resistance adj value with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:54

L10	246	memory with resistor with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:55
L11	0	memory with resistor adj value with light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 21:58
L12	131	phase adj change same resistance same light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 22:00
L13	17	phase-change same resistance same light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 22:03
L14	2	memory same phase-change same resistance same light	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 22:03
S18	4571	rom and resistance adj value	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:10
S19	4	rom and resistance adj value and conductive adj rows and conductive adj columns	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:10
S20	1432	non-volatile adj memory and resistance adj value	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:12
S21	1447	non-volatile near memory and resistance adj value	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:11
S22	4	non-volatile adj memory and resistance adj value and conductive adj rows and conductive adj columns	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:12

S23	529	non-volatile adj memory and resistance adj value and rows and columns	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:12
S24	341	non-volatile adj memory and resistance adj value and rows and columns and logic\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:14
S25	12	non-volatile adj memory and resistance adj value and rows and columns and logic\$2 adj bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/01 12:29
S26	1	"6496416".PN.	USPAT	OR	OFF	2004/09/19 16:19
S27	1	"6235574".PN.	USPAT	OR	OFF	2004/09/19 16:19
S28	1	"5972756".PN.	USPAT	OR	OFF	2004/09/19 16:19
S29	1	"5821160".PN.	USPAT	OR	OFF	2004/09/19 16:19
S30	1	"6261964".PN.	USPAT	OR	OFF	2004/09/19 16:20
S31	1	"6235574".PN.	USPAT	OR	OFF	2004/09/19 16:20
S32	1	"6496416".PN.	USPAT	OR	OFF	2004/09/19 16:20
S33	1	"6261964".PN.	USPAT	OR	OFF	2004/09/19 16:20
S34	1	"6235574".PN.	USPAT	OR	OFF	2004/09/19 16:20
S35	1	"5972756".PN.	USPAT	OR	OFF	2004/09/19 16:20
S36	1	"5656528".PN.	USPAT	OR	OFF	2004/09/19 16:20
S37	1	"5962910".PN.	USPAT	OR	OFF	2004/09/19 16:20
S38	1	"5298784".PN.	USPAT	OR	OFF	2004/09/19 16:21
S39	1	"6496416".PN.	USPAT	OR	OFF	2004/09/19 16:21
S40	8	"6496416"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:21
S41	1	"6495424".PN.	USPAT	OR	OFF	2004/09/19 16:21
S42	0	"2002/0022326".PN.	USPAT	OR	OFF	2004/09/19 16:22
S43	0	"2002/0022326".PN.	USPAT	OR	OFF	2004/09/19 16:22
S44	507	(438/381).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 16:26

S45	291	(438/382).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 16:28
S46	375	(257/528).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 16:28
S47	1235	(257/536).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 16:28
S48	5	((257/536).CCLS.) and non-volatile adj memory and logic\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:29
S49	0	brandenberger-sarah.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:49
S50	10	bloomquist-darrel.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:48
S51	17	brandenberger-sarah-m.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/19 16:49
S52	1	"6587371".PN.	USPAT	OR	OFF	2004/09/19 16:51
S53	1	"6462979".PN.	USPAT	OR	OFF	2004/09/19 16:52
S54	1	"6256224".PN.	USPAT	OR	OFF	2004/09/19 16:54
S55	1	"6191972".PN.	USPAT	OR	OFF	2004/09/19 16:54
S56	1	"6587371".PN.	USPAT	OR	OFF	2004/09/19 16:54
S60	1	"6314014".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:22
S61	1	"6188615".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:25
S62	1	"6128239".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:28

S63	437	mram and resistance adj value and rows and columns	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/01 12:29
S64	11	mram and resistance adj value and rows and columns and logic adj bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/01 12:30
S65	1	"5539697".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:31
S66	1	"4442507".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:31
S67	1	"3863231".PN.	USPAT; USOCR	OR	ON	2005/02/01 12:31